TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

# GT60N323

#### Voltage Resonance Inverter Switching Application

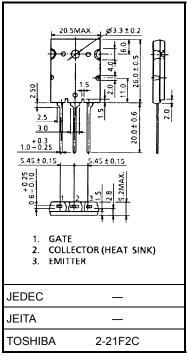
Unit: mm

- diode included between emitter and collector
- Enhancement mode type
- High speed IGBT :  $t_f = 0.19 \mu s$  (typ.) ( $I_C = 60 A$ )

diode :  $t_{rr} = 0.35 \mu s \text{ (max.)} (di/dt = -200 \text{ A/}\mu s)$ 

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		symbol	Rating	Unit	
Collector-Emitter Voltage		V <sub>CES</sub>	1050	V	
Gate-Emitter Voltage	V <sub>GES</sub>	±25	V		
Collector Current	DC	I <sub>C</sub>	60	А	
	1 ms	I <sub>CP</sub>	120		
Diode forward current	DC	I <sub>F</sub>	25	Α	
	1 ms	I <sub>FP</sub>	50		
Collector Power Dissipation (Tc = 25°C)		PC	190	W	
Junction Temperature		Tj	150	°C	
Storage Temperature		T <sub>stg</sub>	-55~150	°C	
Screw Torque		_	0.8	N∙m	

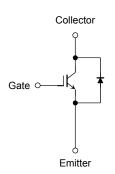


Weight: 9.75 g (typ.)

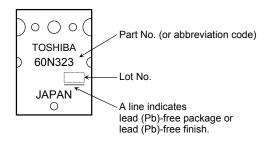
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Equivalent Circuit**



#### Marking



1 2007-05-30



## Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate Leakage Current I <sub>GES</sub>		I <sub>GES</sub>	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0$	_	_	±500	nA
Collector Cut-off Current		I <sub>CES</sub>	V <sub>CE</sub> = 1050 V, V <sub>GE</sub> = 0	_	_	1.0	mA
Gate-Emitter Cut-off Voltage Vo		V <sub>GE</sub> (OFF)	$I_C = 60$ mA, $V_{CE} = 5$ V	6.0	_	9.0	V
Collector-Emitter Saturation Voltage		V <sub>CE (sat)</sub> (1)	I <sub>C</sub> = 10 A, V <sub>GE</sub> = 15 V	_	2.2	2.8	V
Collector-Emitter	-Emitter Saturation Voltage V <sub>CE (sat)</sub> (2) I <sub>C</sub> = 60 A, V <sub>GE</sub> = 15 V		_	2.7	3.3	V	
Input Capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz	_	6800	_	pF
Switching Time	Rise Time	t <sub>r</sub>	30 Ω G G G G G G G G G G G G G G G G G G	_	0.4	_	μs
	Turn-on Time	t <sub>on</sub>		_	0.6	_	
	Fall Time	t <sub>f</sub>		_	0.19	0.25	
	Turn-off Time	t <sub>off</sub>		_	0.5	_	
Diode forward voltage		V <sub>F</sub>	$I_F = 25 \text{ A}, V_{GE} = 0$		_	3.0	V
Reverse Recovery Time t <sub>rr</sub>		t <sub>rr</sub>	$I_F=25~A,~V_{GE}=0,~di/dt=-200~A/\mu s$	_	_	0.35	μS
Thermal Resistance (IGBT)		R <sub>th(j-c)</sub>	_	_	_	0.66	°C/W
Thermal Resistance (diode)		R <sub>th(j-c)</sub>	_	_	_	1.38	°C/W

2 2007-05-30

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3 2007-05-30